

AP10N65F

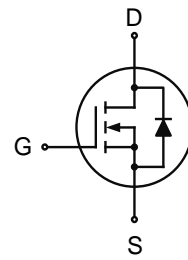
N-Channel Enhancement Mosfet

AIPOWER

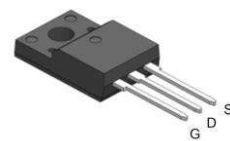
DATA SHEET

Feature

- 650V,10 A
RDS(ON) $\leq 0.88 \Omega$ @ VGS=10V, TYP=0.62 Ω
- Fast Switching
- Low ON Resistance(Rdson $\leq 0.88\Omega$)
- Low Gate Charge (Typical Data:42nC)
- Low Reverse transfer capacitances(Typical:13pF)
- 100% Single Pulse avalanche energy Test
- Halogen Free



Schematic Diagram



TO-220F

Application

- Power switch circuit of adaptor and charger.

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
10N65F	AP10N65F	TO-220F	-	-	1000

ABSOLUTE MAXIMUM RATINGS (T_J=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	650	V
Gate-Source Voltage	V _{GS}	±30	V
Continuous Drain Current (T _C =25°C)	I _D	10	A
Continuous Drain Current (T _C =100°C)	I _D	6.3	A
Pulsed Drain Current ⁽¹⁾	I _{DM}	40	A
Peak Diode Recovery dv/dt ⁽³⁾	dv/dt	5	V/us
Power Dissipation	P _D	39	W
Single Pulse Avalanche Energy ⁽²⁾	E _{AS}	145	mJ
Junction to case ⁽⁴⁾	R _{θJC}	3.2	°C/W
Junction to Ambient ⁽⁴⁾	R _{θJA}	62.5	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

MOSFET ELECTRICAL CHARACTERISTICS(T_J=25°C unless otherwise noted)

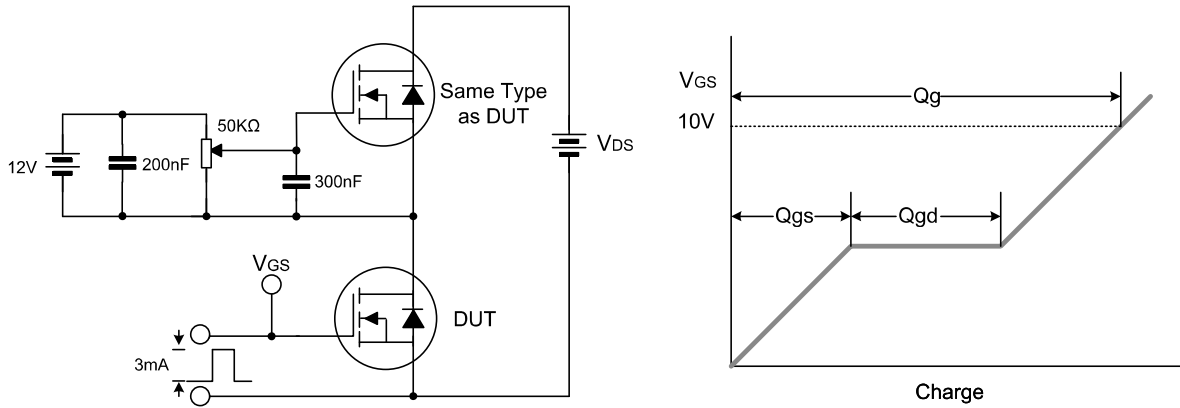
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	650	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =650V, V _{GS} = 0V, T _J =25°C	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±30V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	-	4	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =5A	-	0.62	0.88	Ω
Dynamic characteristics						
Input Capacitance	C _{iSS}	V _{DS} =25V, V _{GS} =0V, f =1MHz	-	1450	-	pF
Output Capacitance	C _{oss}		-	130	-	
Reverse Transfer Capacitance	C _{rSS}		-	13	-	
Forward Transconductance	G _{fs}	V _{DS} =15V, I _D =5A	-	9.5	-	S
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =350V, I _D =10A, V _{GS} =10V, R _G =10Ω	-	25.6	-	ns
Turn-on rise time	t _r		-	32.8	-	
Turn-off delay time	t _{d(off)}		-	210	-	
Turn-off fall time	t _f		-	62	-	
Total Gate Charge	Q _g	V _{DS} =520V, I _D =10A, V _{GS} =10V	-	42	-	nC
Gate-Source Charge	Q _{gs}		-	6.5	-	
Gate-Drain Charge	Q _{gd}		-	20.2	-	
Source-Drain Diode characteristics						
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =10A	-	-	1.5	V
Diode Forward current	I _S		-	-	10	A
Body Diode Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _F =10A,		360		ns
Body Diode Reverse Recovery Charge	Q _{rr}	dI _F /dt=100A/μs		4.5		uC

Notes:

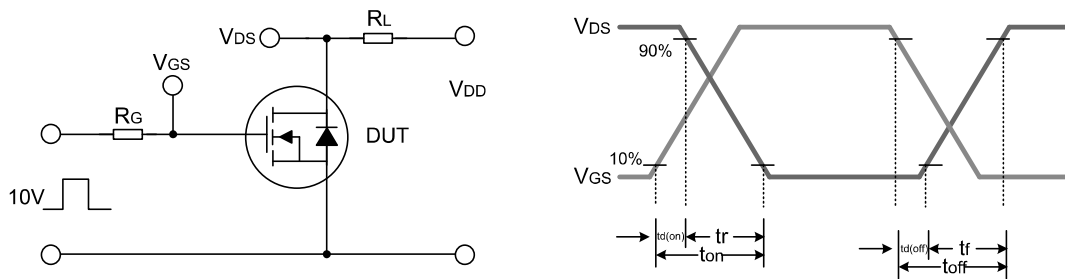
1. Repetitive Rating;pulse width limited by maximum junction temperature.
2. L=10mH,R_g=25Ω,I_{AS}=5.5A , starting T_J=25°C.
3. I_{SD}=12A,dI/dt≤100A/us,V_{DD}≤BV_{DSS},starting T_J=25°C.
4. Repetitive rating; pulse width limited by maximum junction tempera

Test Circuit

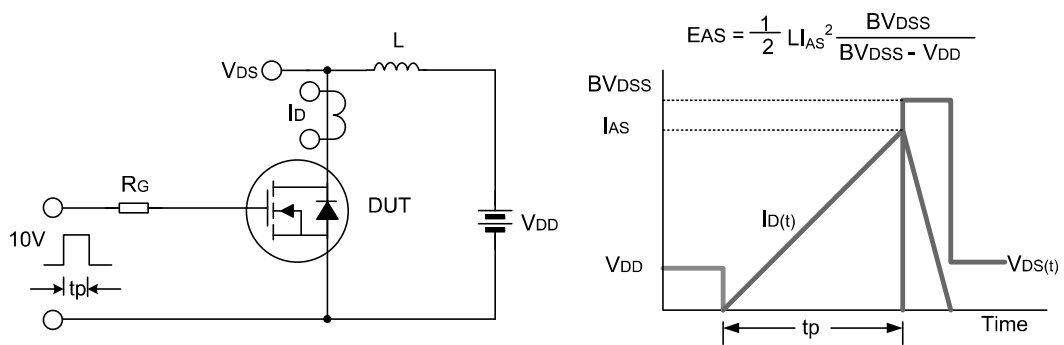
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveform



Typical Performance Characteristics

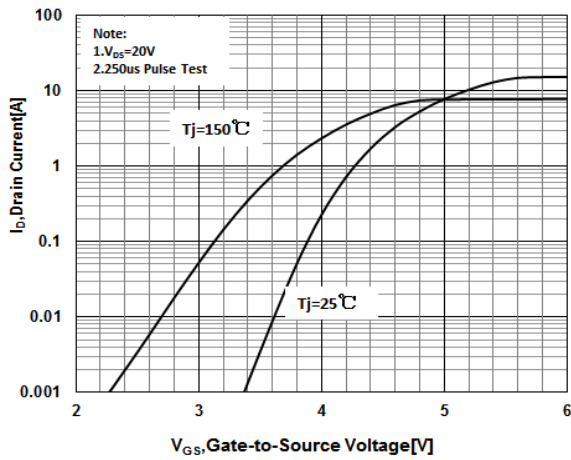


Figure 1 Typical Transfer Characteristics

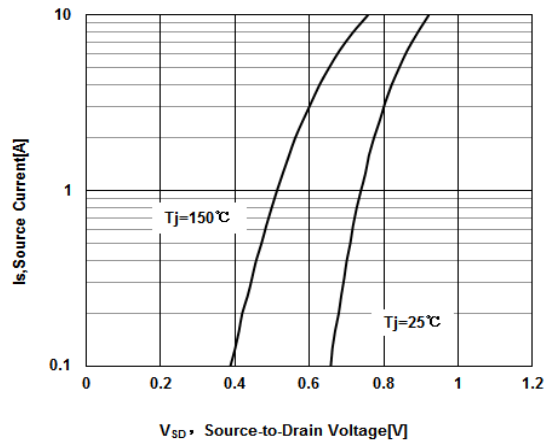


Figure 2 Typical Body Diode Transfer Characteristics

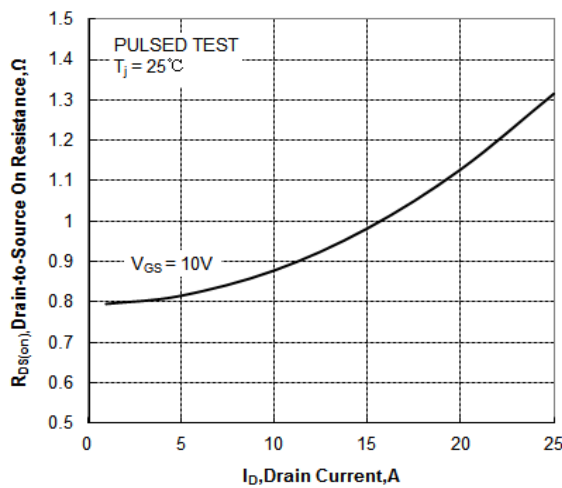


Figure 3 Typical Drain to Source ON Resistance vs Drain Current

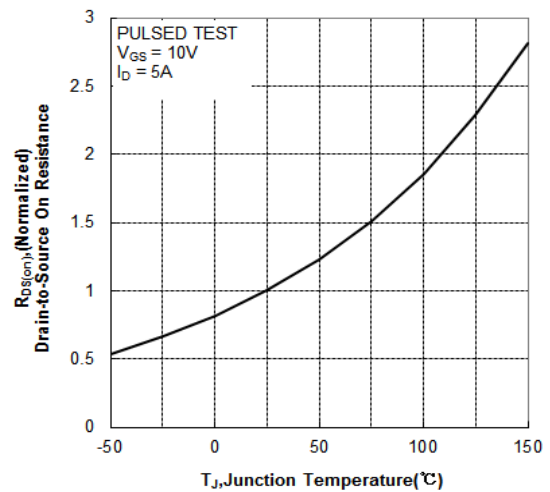


Figure 4 Typical Drain to Source on Resistance vs Junction Temperature

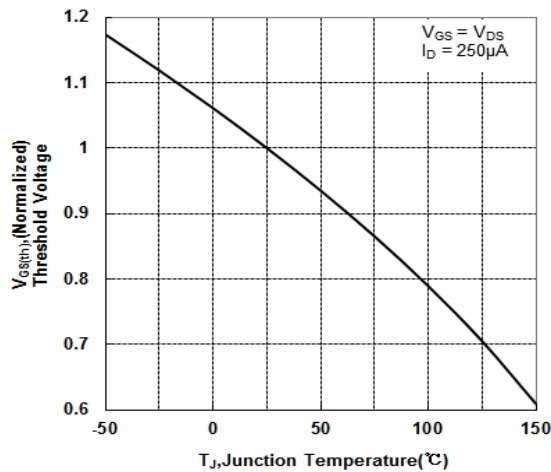


Figure 5 Typical Threshold Voltage vs Junction Temperature

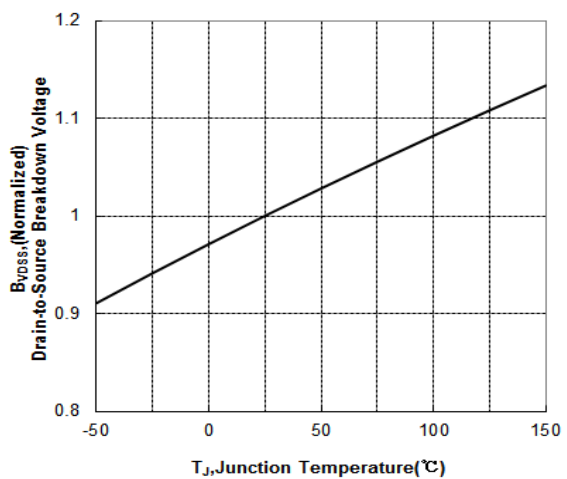


Figure 6 Typical Breakdown Voltage vs Junction Temperature

Typical Performance Characteristics

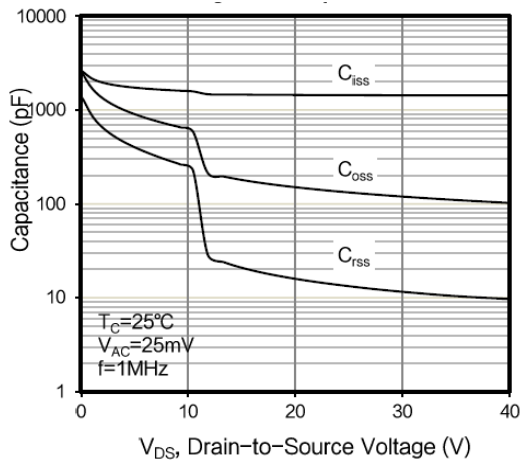


Figure 7 Typical Capacitance vs Drain to Source Voltage

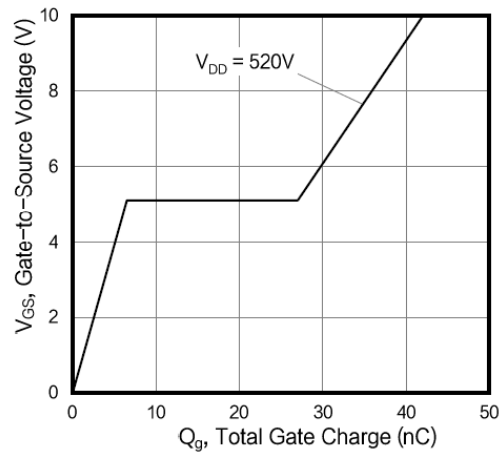


Figure 8 Typical Gate Charge vs Gate to Source Voltage

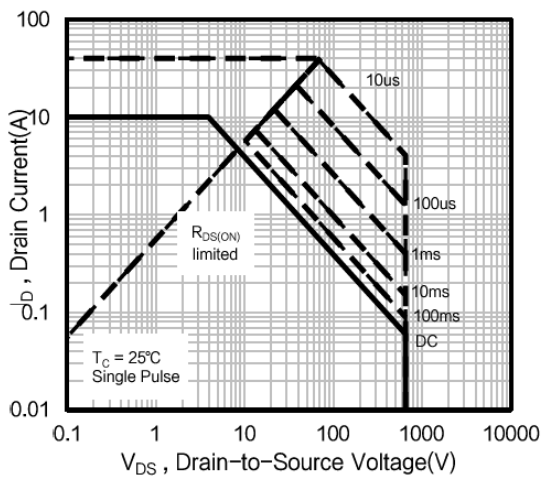


Figure 9 Maximum Forward Bias Safe Operating Area

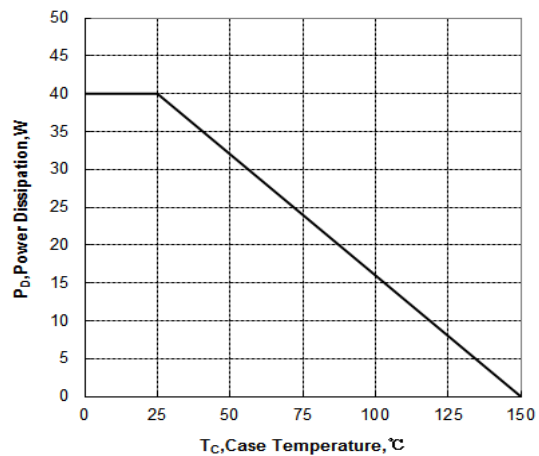


Figure 10 Maximum Power dissipation vs Case Temperature

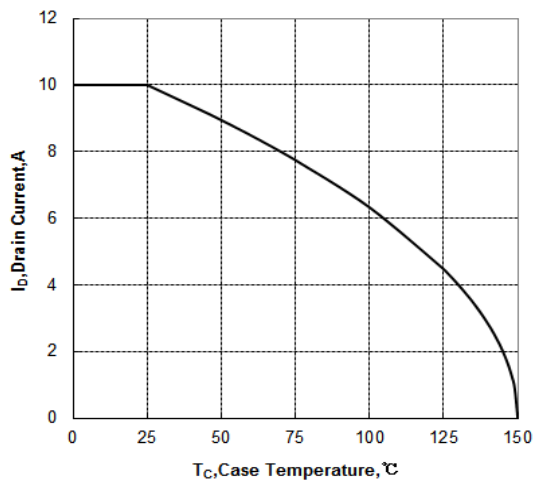


Figure 11 Maximum Continuous Drain Current vs Case Temperature

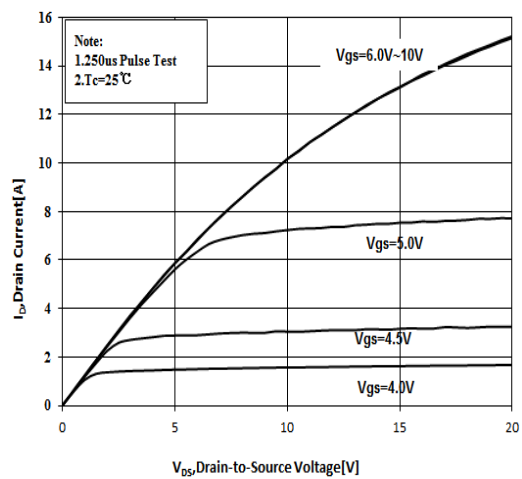


Figure 12 Typical Output Characteristics

Typical Performance Characteristics

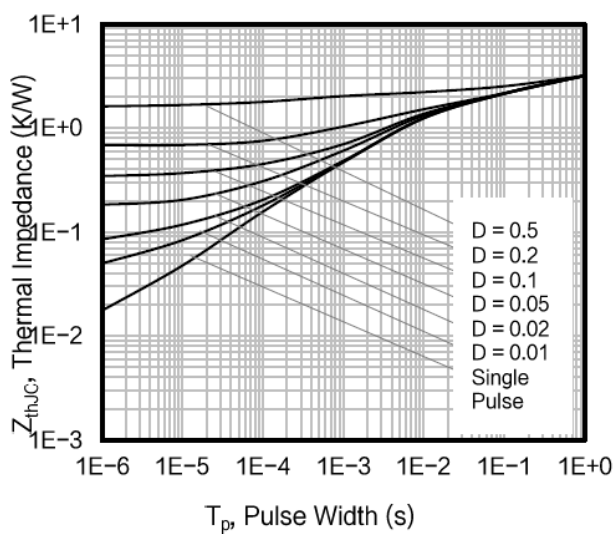
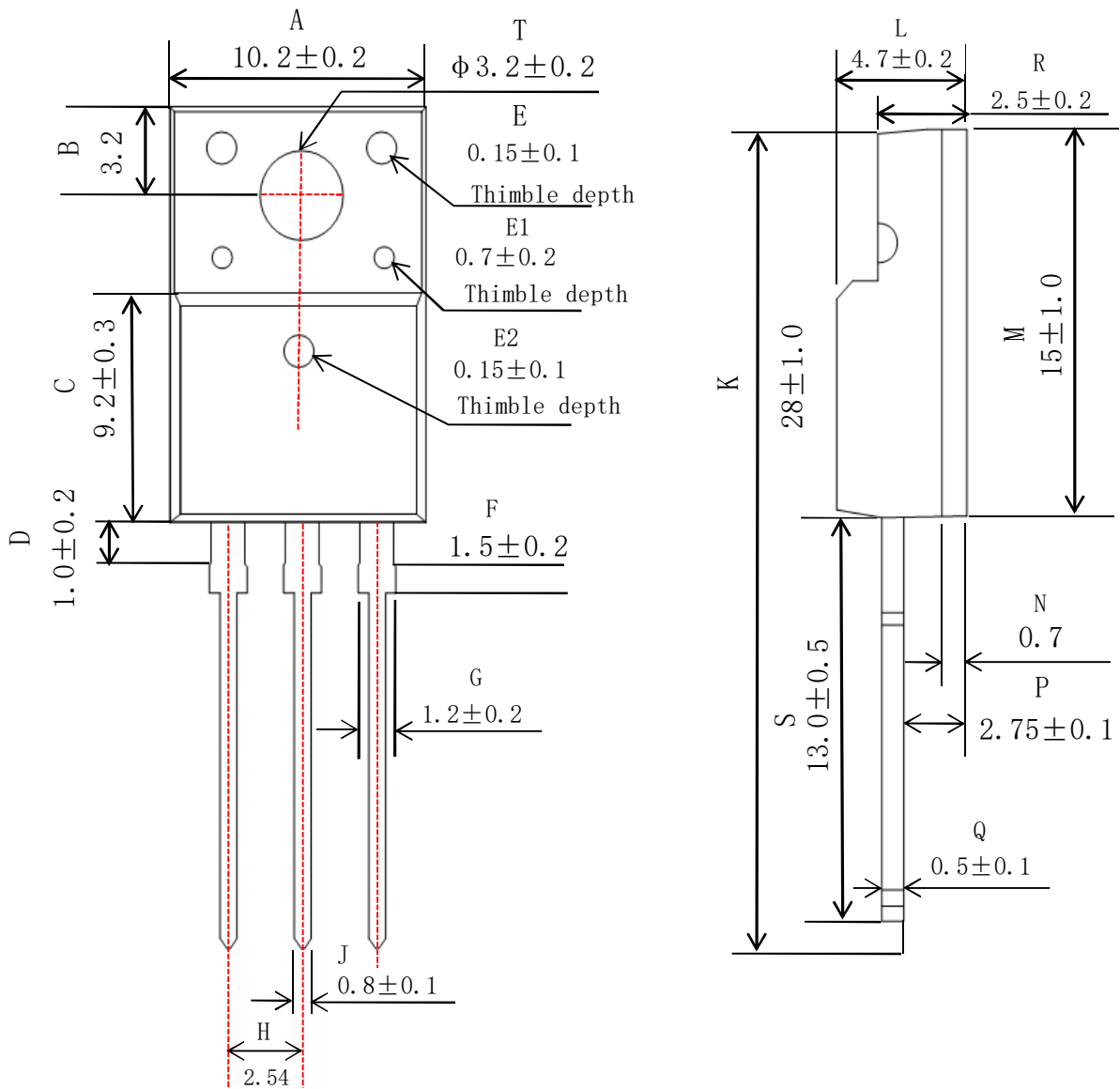


Figure 13 Maximum Effective Thermal Impedance , Junction to Case

Package Dimensions of TO-220F

Note: UNIT: mm



Revision History

Revision	Release	Remark
V1.0	2023/10/07	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Allpower assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which requires high reliability. Customers using or selling these products for use in medical, life-saving, or life-sustaining applications do so at their own risk and agree to fully indemnify.

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